Inventor: Robert J. Hillard "METHOD OF ELECTRICAL CHARACTERIZATION OF A SILICON-ON-INSULATOR (SOI) WAFER" Attorney Docket No.: 1880-031249 Application No.: 10/701,841 34 MEASUREMENT APPLYING ELECTRICAL MEANS FOR STIMULUS MEANS CHUCK SEMICONDUCTOR SUBSTRATE ELECTRIC VACUUM 36 CONTACT FORMING MEANS 28

Inventor: Robert J. Hillard "METHOD OF ELECTRICAL CHARACTERIZATION OF A SILICON-ON-INSULATOR (SOI)

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WAFER"
Attorney Docket No.: 1880-031249 Application No.: 10/701,841

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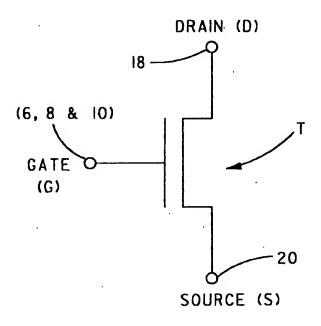


FIG. 2

Inventor: Robert J. Hillard

"METHOD OF ELECTRICAL CHARACTERIZATION OF A SILICON-ON-INSULATOR (SOI)

WAFER"

Attorney Docket No.: 1880-031249 Application No.: 10/701,841

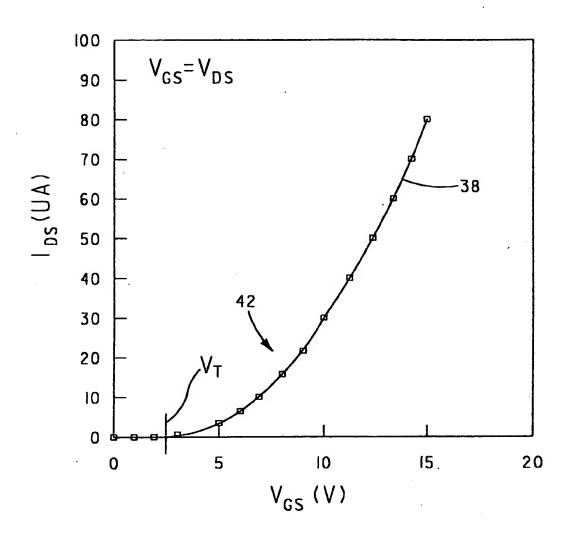


FIG. 3

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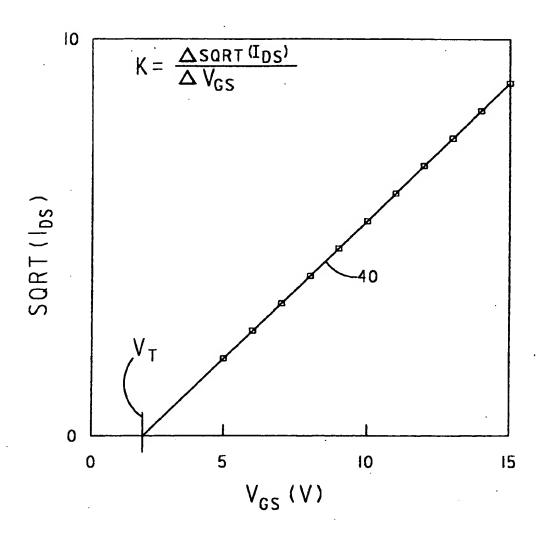


FIG. 4

Inventor: Robert J. Hillard "METHOD OF ELECTRICAL CHARACTERIZATION OF A SILICON-ON-INSULATOR (SOI)
WAFER"
Attorney Docket No.: 1880-031249 Application No.: 10/701,841

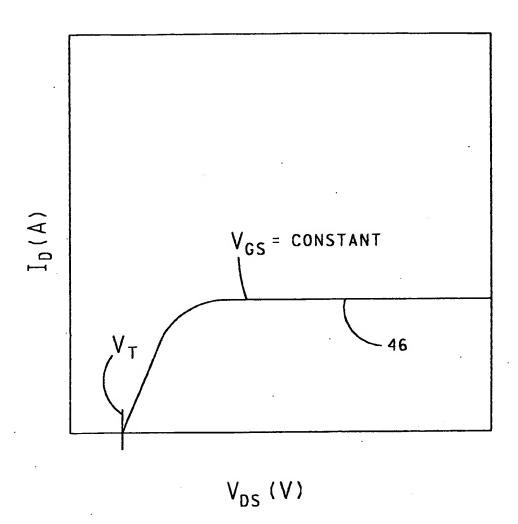


FIG. 6



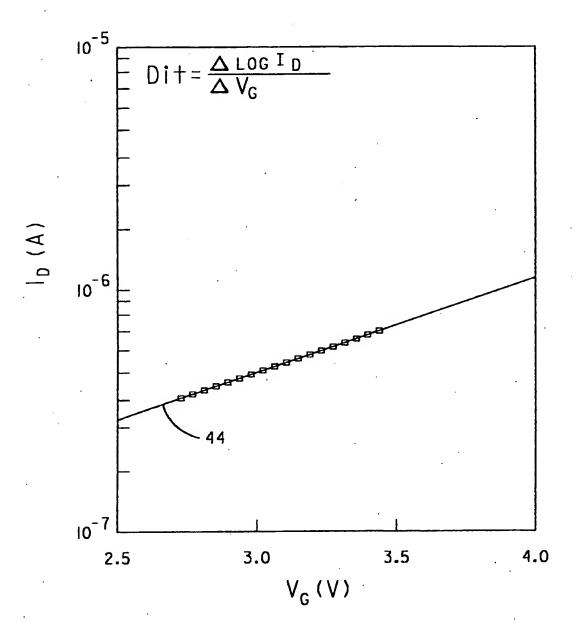


FIG. 5